

CS-99-065



October 16, 2001

1765  
COPY OF PAPERS  
ORIGINALLY FILED

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572  
20 McIntosh Drive  
Poughkeepsie, N.Y. 12603

RECEIVED  
MAR 08 2002  
TC 1700 #12  
3/22/02  
RW

Subject:

Serial No. 09/442,499 11/18/99

Paul Kwok Keung Ho, Xue Chun Dai

PLASMA ETCH METHOD FOR FORMING  
PLASMA ETCHED SILICON LAYER

Grp. Art Unit: 1765

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 5,431,772 to Babie et al., "Selective Silicon  
Nitride Plasma Etching Process," discloses a two step method of  
etching a silicon nitride layer carrying a surface oxygen film  
from a substrate in a plasma reactor.

CS-99-065

European Pat nt 0 272 143 A2 to Jerry Yuen Kul Wong et al., "Bromine and Iodin Etch Process for Silicon and Silicides," discloses a process for etching single crystal silicon, polysilicon, silicide and polycide using iodinate or brominate gas chemistry.

Sincerely,

A handwritten signature in cursive script, appearing to read "Stephen B. Ackerman".

Stephen B. Ackerman,  
Reg. No. 37761